3.3 V quad buffer; 3-state Rev. 7 — 31 May 2016

**Product data sheet** 

### 1. General description

The 74LVT125; 74LVTH125 is a high-performance BiCMOS product designed for  $V_{CC}$  operation at 3.3 V.

This device combines low static and dynamic power dissipation with high speed and high output drive. The 74LVT125; 74LVTH125 device is a quad buffer that is ideal for driving bus lines. The device features four output enable inputs (1OE, 2OE, 3OE and 4OE), each controlling one of the 3-state outputs.

### 2. Features and benefits

- Quad bus interface
- 3-state buffers
- Output capability: +64 mA and -32 mA
- TTL input and output switching levels
- Input and output interface capability to systems at 5 V supply
- Bus hold data inputs eliminate need for external pull-up resistors to hold unused inputs
- Live insertion and extraction permitted
- No bus current loading when output is tied to 5 V bus
- Power-up 3-state
- Latch-up protection:
  - JESD78: exceeds 500 mA
- ESD protection:
  - MIL STD 883 method 3015: exceeds 2000 V
  - Machine model: exceeds 200 V



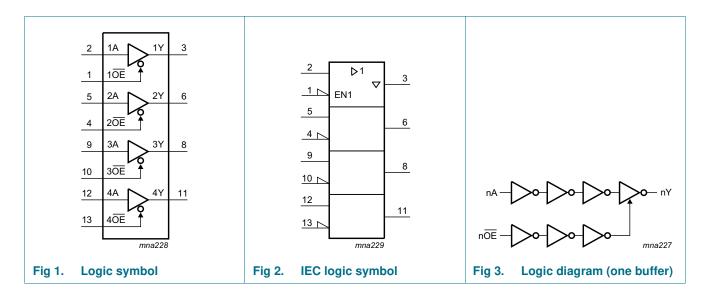
3.3 V quad buffer; 3-state

### 3. Ordering information

#### Table 1. Ordering information

Type number	Package						
	Temperature range	Name	Description	Version			
74LVT125D	–40 °C to +85 °C	SO14	plastic small outline package; 14 leads;	SOT108-1			
74LVTH125D			body width 3.9 mm				
74LVT125DB	–40 °C to +85 °C	SSOP14	plastic shrink small outline package; 14 leads;	SOT337-1			
74LVTH125DB			body width 5.3 mm				
74LVT125PW	–40 °C to +85 °C	TSSOP14	plastic thin shrink small outline package; 14 leads;	SOT402-1			
74LVTH125PW			body width 4.4 mm				
74LVT125BQ	–40 °C to +85 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very	SOT762-1			
74LVTH125BQ			thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm				

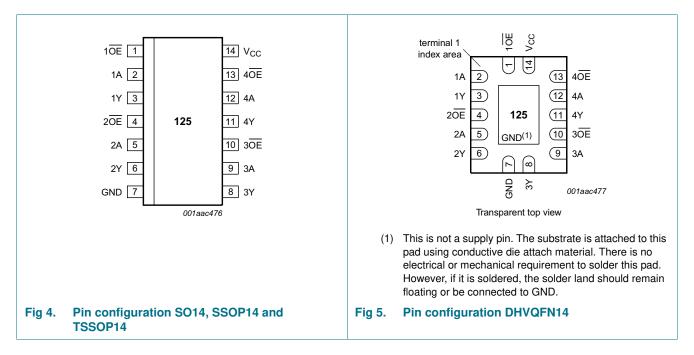
### 4. Functional diagram



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### 5. Pinning information

### 5.1 Pinning



### 5.2 Pin description

### Table 2.Pin description

Symbol	Pin	Description	
1 <del>0E</del>	1	1 output enable input (active LOW)	
1A	2	1 data input	
1Y	3	1 data output	
2 <del>0E</del>	4	2 output enable input (active LOW)	
2A	5	2 data input	
2Y	6	2 data output	
GND	7	ground (0 V)	
3Y	8	3 data output	
3A	9	3 data input	
3 <del>0E</del>	10	3 output enable input (active LOW)	
4Y	11	4 data output	
4A	12	4 data input	
4 <mark>0E</mark>	13	4 output enable input (active LOW)	
V <sub>CC</sub>	14	supply voltage	

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### 6. Functional description

### 6.1 Function table

Table 3. Function table <sup>[1]</sup>							
	Input	Output					
n <mark>OE</mark>	nA	nY					
L	L	L					
L	Н	Н					
Н	X	Z					

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

### 7. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CC</sub>	supply voltage			-0.5	+4.6	V
VI	input voltage		[1]	-0.5	+7.0	V
Vo	output voltage	output in OFF-state or HIGH-state	[1]	-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	V <sub>1</sub> < 0 V		-	-50	mA
I <sub>ОК</sub>	output clamping current	V <sub>O</sub> < 0 V		-	-50	mA
I <sub>O</sub>	output current	output in LOW-state		-	128	mA
		output in HIGH-state		-	-64	mA
T <sub>stg</sub>	storage temperature			-65	+150	°C
Т <sub>ј</sub>	junction temperature		[2]	-	150	°C

[1] The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

[2] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability.

### 8. Recommended operating conditions

#### Table 5. Recommended operating conditions

Min	Тур	Max	Unit
2.7	-	3.6	V
0	-	5.5	V
2.0	-	-	V
-	-	0.8	V
-	-	-32	mA
-	-	32	mA
-	-	64	mA
0	-	10	ns/V
-40	-	+85	°C
al			

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### 9. Static characteristics

### Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
T <sub>amb</sub> = -	40 °C to +85 °C <u>[1]</u>						
V <sub>IK</sub>	input clamping voltage	$I_{IK} = -18 \text{ mA}; V_{CC} = 2.7 \text{ V}$		-	-0.9	-1.2	V
V <sub>OH</sub>	HIGH-level output voltage	$I_{OH} = -100 \ \mu A;$ $V_{CC} = 2.7 \ V \text{ to } 3.6 \ V$		$V_{CC}-0.2$	$V_{CC}-0.1$	-	V
		$I_{OH} = -8 \text{ mA}; V_{CC} = 2.7 \text{ V}$		2.4	2.5	-	V
		$I_{OH} = -32 \text{ mA}; V_{CC} = 3.0 \text{ V}$		2.0	2.2	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>CC</sub> = 2.7 V					
		I <sub>OL</sub> = 100 μA		-	0.1	0.2	V
		I <sub>OL</sub> = 24 mA		-	0.3	0.5	V
		V <sub>CC</sub> = 3.0 V					
		I <sub>OL</sub> = 16 mA		-	0.25	0.4	V
		I <sub>OL</sub> = 32 mA		-	0.3	0.5	V
		I <sub>OL</sub> = 64 mA		-	0.4	0.55	V
l <sub>l</sub>	input leakage current	all input pins					
		$V_{CC} = 0 V \text{ or } 3.6 V; V_{I} = 5.5 V$		-	1	10	μA
		control pins					
		$V_{CC} = 3.6 \text{ V}; \text{ V}_{I} = \text{V}_{CC} \text{ or GND}$		-	±0.1	±1	μA
		data pins	[2]				
		$V_{CC} = 3.6 \text{ V}; \text{ V}_{I} = \text{V}_{CC}$		-	0.1	1	μA
		$V_{CC} = 3.6 \text{ V}; \text{ V}_{I} = 0 \text{ V}$		-	-1	-5	μA
I <sub>OFF</sub>	power-off leakage current	$V_{CC} = 0 V; V_1 \text{ or } V_0 = 0 V \text{ to } 4.5 V$		-	1	±100	μA
BHL	bus hold LOW current	$V_{CC} = 3 V; V_1 = 0.8 V$	[3]	75	150	-	μA
I <sub>BHH</sub>	bus hold HIGH current	V <sub>CC</sub> = 3 V; V <sub>I</sub> = 2.0 V		-	-150	-75	μA
I <sub>BHLO</sub>	bus hold LOW overdrive current	$V_{CC} = 3.6 \text{ V}; \text{ V}_{I} = 0 \text{ V} \text{ to } 3.6 \text{ V}$		500	-	-	μA
I <sub>BHHO</sub>	bus hold HIGH overdrive current	$V_{CC} = 3.6 \text{ V}; \text{ V}_{I} = 0 \text{ V} \text{ to } 3.6 \text{ V}$		-	-	-500	μA
I <sub>LO</sub>	output leakage current	output in HIGH-state when $V_O > V_{CC}$ ; $V_O = 5.5 V$ ; $V_{CC} = 3.0 V$		-	60	125	μΑ
I <sub>O(pu/pd)</sub>	power-up/power-down output current	$\label{eq:V_CC} \begin{array}{l} V_{CC} \leq 1.2 \ V; \ V_O = 0.5 \ V \ to \ V_{CC}; \\ V_{\underline{l}} = GND \ or \ V_{CC}; \\ n\overline{OE} = don't \ care \end{array}$	[4]	-	±1	±100	μA
loz	OFF-state output current	$V_{CC}$ = 3.6 V; $V_I$ = $V_{IH}$ or $V_{IL}$					
		output HIGH: V <sub>O</sub> = 3.0 V		-	1	5	μA
		output LOW: V <sub>O</sub> = 0.5 V		-	-1	-5	μA

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CC</sub>	supply current	$\label{eq:V_CC} \begin{array}{l} V_{CC} = 3.6 \ \text{V}; \ \text{V}_{\text{I}} = \text{GND or } \ \text{V}_{CC}; \\ \text{I}_{O} = 0 \ \text{A} \end{array}$					
		outputs HIGH		-	0.13	0.19	mA
		outputs LOW		-	2	7	mA
		outputs disabled	<u>[5]</u>	-	0.13	0.19	mA
Δl <sub>CC</sub>	additional supply current	per input pin; $V_{CC} = 3 V$ to 3.6 V; one input at $V_{CC} - 0.6 V$ and other inputs at $V_{CC}$ or GND	<u>[6]</u>	-	0.1	0.2	mA
CI	input capacitance	V <sub>I</sub> = 0 V or 3.0 V		-	4	-	pF
Co	output capacitance	outputs disabled; $V_O = 0 V \text{ or } 3.0 V$		-	8	-	pF

#### Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

[1] Typical values are measured at  $V_{CC}$  = 3.3 V and  $T_{amb}$  = 25 °C.

[2] Unused pins at  $V_{CC}$  or GND.

[3] This is the bus hold overdrive current required to force the input to the opposite logic state.

[4] This parameter is valid for any V<sub>CC</sub> between 0 V and 1.2 V with a transition time of up to 10 ms. From V<sub>CC</sub> = 1.2 V to V<sub>CC</sub> = 3.0 V to 3.6 V a transition time of 100  $\mu$ s is permitted. This parameter is valid for T<sub>amb</sub> = 25 °C only.

[5]  $I_{CC}$  is measured with outputs pulled to  $V_{CC}$  or GND.

[6] This is the increase in supply current for each input at the specified voltage level other than V<sub>CC</sub> or GND.

### **10. Dynamic characteristics**

#### Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>amb</sub> = –	40 °C to +85 °C[1]		I	1		
t <sub>PLH</sub>	LOW to HIGH propagation delay	nAn to nY; see Figure 6				
		V <sub>CC</sub> = 2.7 V	-	-	4.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.0	2.7	4.0	ns
t <sub>PHL</sub>	HIGH to LOW propagation delay	nAn to nY; see Figure 6				
		V <sub>CC</sub> = 2.7 V	-	-	4.9	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.0	2.9	3.9	ns
t <sub>PZH</sub>	OFF-state to HIGH propagation delay	nOE to nY; see Figure 7				
		V <sub>CC</sub> = 2.7 V	-	-	6.0	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.0	3.4	4.7	ns
t <sub>PZL</sub>	OFF-state to LOW propagation delay	nOE to nY; see Figure 7				
		V <sub>CC</sub> = 2.7 V	-	-	6.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.1	3.4	4.7	ns
t <sub>PHZ</sub>	HIGH to OFF-state propagation delay	nOE to nY; see Figure 7				
		V <sub>CC</sub> = 2.7 V	-	-	5.7	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.8	3.7	5.1	ns

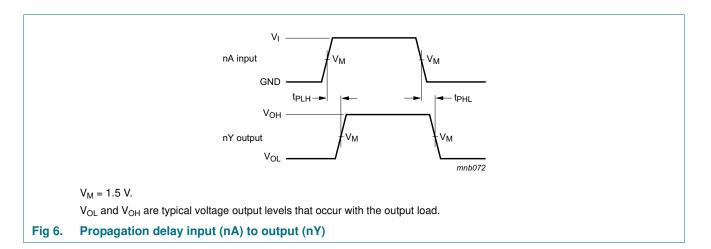
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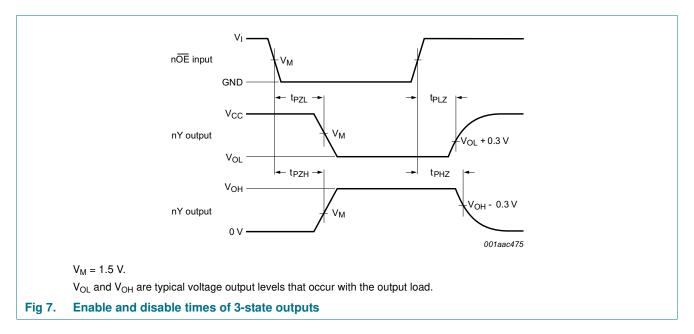
Voltages are referenced to GND (ground = $0 V$ ); for test circuit see <u>Figure 8</u> .								
Symbol	Parameter	Conditions	Min Typ Max			Unit		
t <sub>PLZ</sub>	LOW to OFF-state propagation delay	nOE to nY; see Figure 7						
		$V_{CC} = 2.7 V$	-	-	4.0	ns		
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.3	2.6	4.5	ns		

 Table 7.
 Dynamic characteristics ...continued

[1] Typical values are at  $V_{CC}$  = 3.3 V and  $T_{amb}$  = 25 °C.

### 11. Waveforms

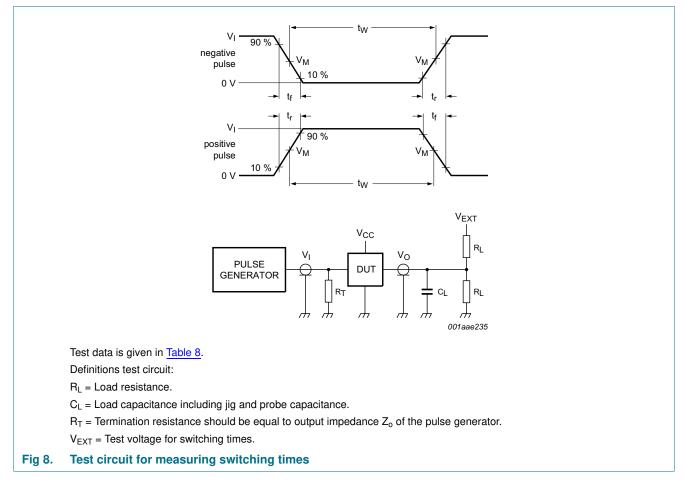




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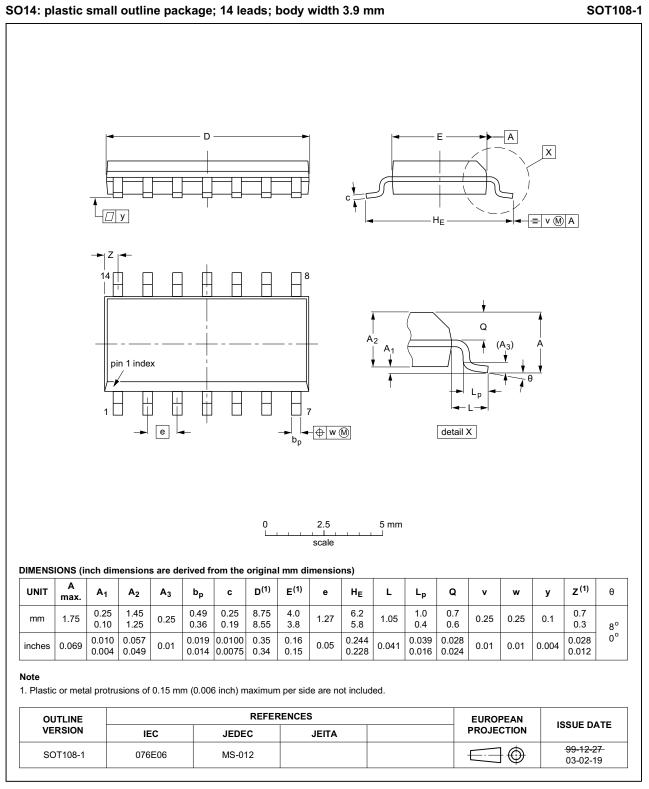


#### Table 8. Test data

Input				Load		V <sub>EXT</sub>		
٧ <sub>I</sub>	f <sub>i</sub>	tw	t <sub>r</sub> , t <sub>f</sub>	CL	RL	t <sub>PHZ</sub> , t <sub>PZH</sub>	t <sub>PLZ</sub> , t <sub>PZL</sub>	t <sub>PLH</sub> , t <sub>PHL</sub>
2.7 V	≤ 10 MHz	500 ns	≤ 2.5 ns	50 pF	500 Ω	GND	6 V	open

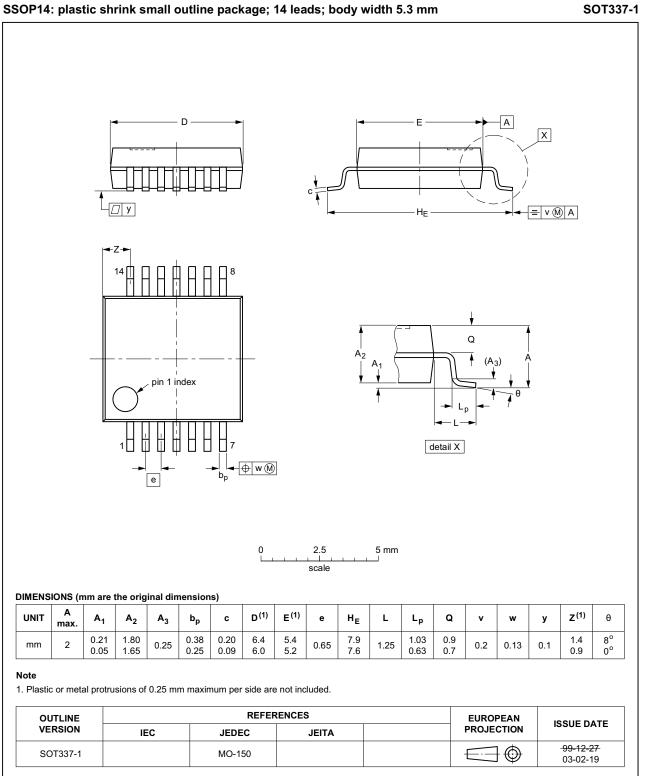
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### 12. Package outline



#### Fig 9. Package outline SOT108-1 (SO14)

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### Fig 10. Package outline SOT337-1 (SSOP14)

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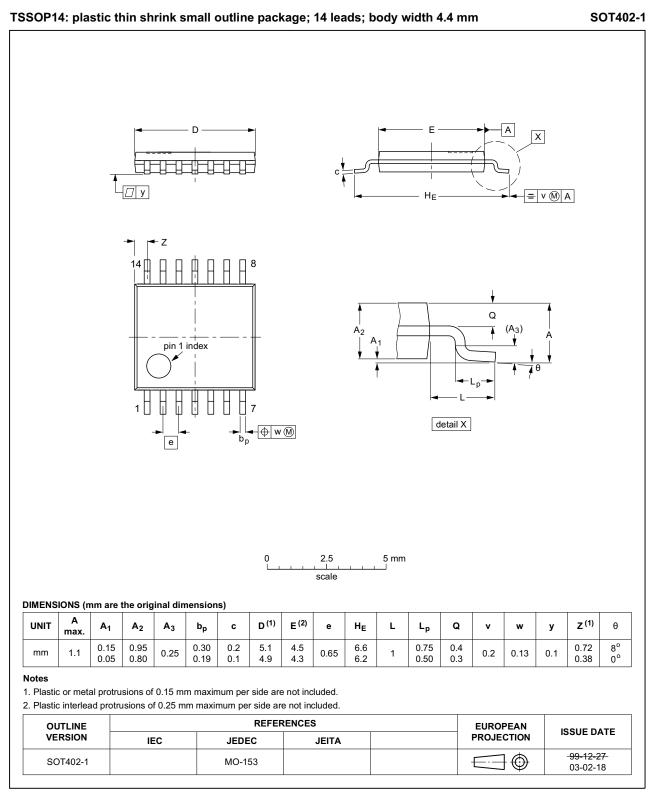
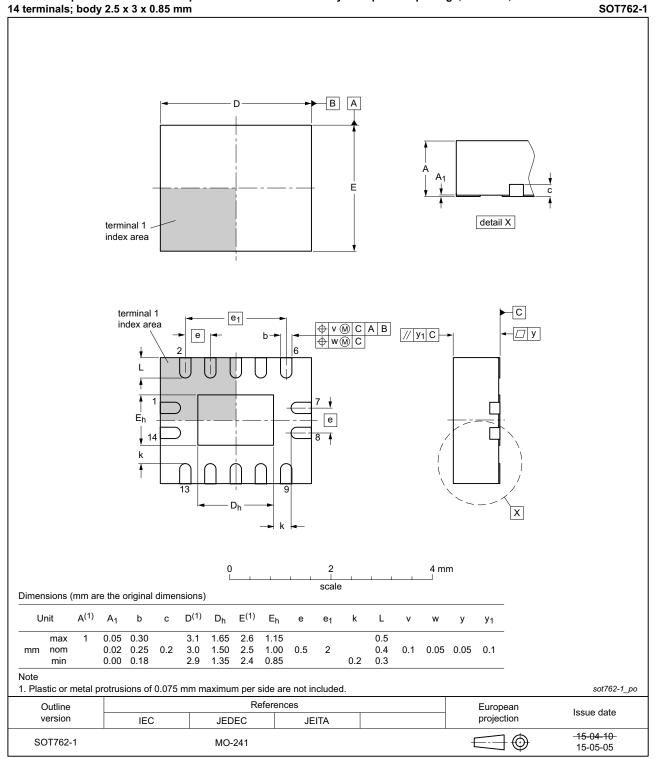


Fig 11. Package outline SOT402-1 (TSSOP14)

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DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads;

### Fig 12. Package outline SOT762-1 (DHVQFN14)

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### **13. Abbreviations**

Table 9. Abbreviations						
Acronym	Description					
CMOS	Complementary Metal Oxide Semiconductor					
DUT	Device Under Test					
ESD	ElectroStatic Discharge					
TTL	Transistor-Transistor Logic					

### 14. Revision history

### Table 10.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes				
74LVT_LVTH125 v.7	20160531	Product data sheet	-	74LVT125 v.6				
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> </ul>							
	<ul> <li>Legal texts h</li> </ul>	have been adapted to the ne	w company name where	e appropriate.				
74LVT_LVTH125 v.6	20060306	Product data sheet	-	74LVT125 v.5				
Modifications:	• Section 3: A 74LVTH125	dded type numbers 74LVTH BQ.	125D, 74LVTH125DB, 7	74LVTH125PW and				
74LVT125 v.5	20050210	Product data sheet	-	74LVT125 v.4				
74LVT125 v.4	20050207	Product data sheet	-	74LVT125 v.3				
74LVT125 v.3	20040624	Product data sheet	-	74LVT125 v.2				
74LVT125 v.2	19980219	Product specification	-	74LVT125 v.1				
74LVT125 v.1	-	-	-	-				

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Document status[1][2]	Product status <sup>[3]</sup>	Definition
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Date of release: 31 May 2016 Document identifier: 74LVT\_LVTH125